Abstracts

Design of Medium Power, 6-12 GHz GaAs FET Amplifier, Using High Dielectric Networks

S.D. McCarter and A.M. Pavio. "Design of Medium Power, 6-12 GHz GaAs FET Amplifier, Using High Dielectric Networks." 1982 MTT-S International Microwave Symposium Digest 82.1 (1982 [MWSYM]): 159-161.

The input and output networks for a 4800 µm (four 1200 µm cells) gallium arsenide FET amplifier were successfully developed and constructed on high dielectric substrate material using distributed transmission line techniques. This paper describes the design and fabrication of the input and output networks and the performance of a completed 6-12 GHz 4 watt amplifier.

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